



FSD176MRT

Green-Mode Fairchild Power Switch (FPS™)

Features

- Advanced Soft Burst-Mode Operation for Low Standby Power and Low Audible Noise
- Random Frequency Fluctuation for Low EMI
- Pulse-by-Pulse Current Limit
- Various Protection Functions: Overload Protection (OLP), Over-Voltage Protection (OVP), Abnormal Over-Current Protection (AOCP), Internal Thermal Shutdown (TSD) with Hysteresis, Output-Short Protection (OSP), and Under-Voltage Lockout (UVLO) with Hysteresis
- Low Operating Current (0.4mA) in Burst Mode
- Internal Startup Circuit
- Internal High-Voltage SenseFET: 650V
- Built-in Soft-Start: 15ms
- Auto-Restart Mode

Description

The FSD176MRT is an integrated Pulse Width Modulation (PWM) controller and SenseFET specifically designed for offline Switch-Mode Power Supplies (SMPS) with minimal external components. The PWM controller includes an integrated fixed-frequency oscillator, Under-Voltage Lockout (UVLO), Leading-Edge Blanking (LEB), optimized gate driver, internal soft-start, temperature-compensated precise current sources for loop compensation, and self-protection circuitry. Compared with a discrete MOSFET and PWM controller solution, the FSD176MRT can reduce total cost, component count, size, and weight; while simultaneously increasing efficiency, productivity, and system reliability. This device provides a basic platform for cost-effective design of a flyback converter.

Applications

- Power Supply for LCD Monitor, STB, and DVD Combination

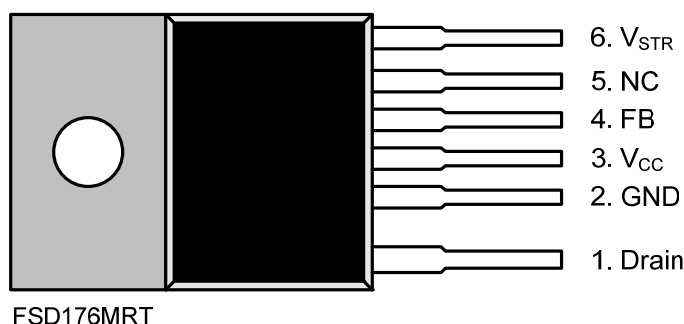
Ordering Information

Part Number	Package	Operating Junction Temperature	Current Limit	R _{DS(ON)} (Max.)	Output Power Table ⁽²⁾				Replaces Device
					230V _{AC} ±15% ⁽³⁾		85~265V _{AC}		
					Adapter ⁽⁴⁾	Open Frame ⁽⁵⁾	Adapter ⁽⁴⁾	Open Frame ⁽⁵⁾	
FSD176MRTUDTU	TO-220 6-Lead ⁽¹⁾ U-Forming	-40°C ~ +125°C	3.50A	1.6Ω	80W	90W	48W	70W	FSGM0765R
FSD176MRTLDTU	TO-220 6-Lead ⁽¹⁾ L-Forming	-40°C ~ +125°C	3.50A	1.6Ω	80W	90W	48W	70W	FSGM0765R

Notes:

1. Pb-free package per JEDEC J-STD-020B.
2. The junction temperature can limit the maximum output power.
3. 230V_{AC} or 100/115V_{AC} with voltage doubler.
4. Typical continuous power in a non-ventilated enclosed adapter measured at 50°C ambient temperature.
5. Maximum practical continuous power in an open-frame design at 50°C ambient temperature.

Pin Configuration



FSD176MRT

Figure 3. Pin Configuration (Top View)

Pin Definitions

Pin #	Name	Description
1	Drain	SenseFET Drain. High-voltage power SenseFET drain connection.
2	GND	Ground. This pin is the control ground and the SenseFET source.
3	V _{CC}	Power Supply. This pin is the positive supply input, which provides the internal operating current for both startup and steady-state operation.
4	FB	Feedback. This pin is internally connected to the inverting input of the PWM comparator. The collector of an opto-coupler is typically tied to this pin. For stable operation, a capacitor should be placed between this pin and GND. If the voltage of this pin reaches 7V, the overload protection triggers, which shuts down the FPS.
5	NC	No Connection
6	V _{STR}	Startup. This pin is connected directly, or through a resistor, to the high-voltage DC link. At startup, the internal high-voltage current source supplies internal bias and charges the external capacitor connected to the V _{CC} pin. Once V _{CC} reaches 12V, the internal current source (I _{CH}) is disabled.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter		Min.	Max.	Unit
V_{STR}	V_{STR} Pin Voltage			650	V
V_{DS}	Drain Pin Voltage			650	V
V_{CC}	V_{CC} Pin Voltage			26	V
V_{FB}	Feedback Pin Voltage		-0.3	12.0	V
I_{DM}	Drain Current Pulsed			12.8	A
I_{DS}	Continuous Switching Drain Current ⁽⁶⁾	$T_C=25^{\circ}\text{C}$		6.4	A
		$T_C=100^{\circ}\text{C}$		4.0	A
E_{AS}	Single Pulsed Avalanche Energy ⁽⁷⁾			390	mJ
P_D	Total Power Dissipation ($T_C=25^{\circ}\text{C}$) ⁽⁸⁾			50	W
T_J	Maximum Junction Temperature			150	$^{\circ}\text{C}$
	Operating Junction Temperature ⁽⁹⁾		-40	+125	$^{\circ}\text{C}$
T_{STG}	Storage Temperature		-55	+150	$^{\circ}\text{C}$
ESD	Electrostatic Discharge Capability	Human Body Model, JESD22-A114	4.5		kV
		Charged Device Model, JESD22-C101	2.0		

Notes:

6. Repetitive peak switching current when the inductive load is assumed: Limited by maximum duty ($D_{MAX}=0.74$) and junction temperature (see Figure 4.).
7. $L=45\text{mH}$, starting $T_J=25^{\circ}\text{C}$.
8. Infinite cooling condition (refer to the SEMI G30-88).
9. Although this parameter guarantees IC operation, it does not guarantee all electrical characteristics.

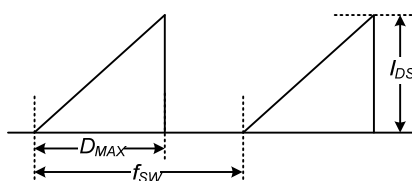


Figure 4. Repetitive Peak Switching Current

Thermal Impedance

$T_A=25^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Value	Unit
θ_{JA}	Junction-to-Ambient Thermal Impedance ⁽¹⁰⁾	63.5	$^{\circ}\text{C/W}$
θ_{JC}	Junction-to-Case Thermal Impedance ⁽¹¹⁾	2.5	$^{\circ}\text{C/W}$

Notes:

10. Free standing without heat sink under natural convection condition, per JEDEC 51-2 and 1-10.
11. Infinite cooling condition per Mil Std. 883C method 1012.1.

Electrical Characteristics

$T_J = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
SenseFET Section						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{CC} = 0V, I _D = 250μA	650			V
I _{DSS}	Zero-Gate-Voltage Drain Current	V _{DS} = 650V, T _A = 25°C			250	μA
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =1A		1.3	1.6	Ω
C _{ISS}	Input Capacitance ⁽¹²⁾	V _{DS} = 25V, V _{GS} = 0V, f=1MHz		674		pF
C _{OSS}	Output Capacitance ⁽¹²⁾	V _{DS} = 25V, V _{GS} = 0V, f=1MHz		93		pF
t _r	Rise Time	V _{DS} = 325V, I _D = 4A, R _G =25Ω		30		ns
t _f	Fall Time	V _{DS} = 325V, I _D = 4A, R _G =25Ω		26		ns
t _{d(on)}	Turn-On Delay	V _{DS} = 325V, I _D = 4A, R _G =25Ω		16		ns
t _{d(off)}	Turn-Off Delay	V _{DS} = 325V, I _D = 4A, R _G =25Ω		39		ns
Control Section						
f _S	Switching Frequency ⁽¹²⁾	V _{CC} = 14V, V _{FB} = 4V	61	67	73	kHz
Δf _S	Switching Frequency Variation ⁽¹²⁾	−25°C < T _J < 125°C		±5	±10	%
D _{MAX}	Maximum Duty Ratio	V _{CC} = 14V, V _{FB} = 4V	61	67	73	%
D _{MIN}	Minimum Duty Ratio	V _{CC} = 14V, V _{FB} = 0V				%
I _{FB}	Feedback Source Current	V _{FB} =0V	65	90	115	μA
V _{START}	UVLO Threshold Voltage	V _{FB} = 0V, V _{CC} Sweep	11	12	13	V
V _{STOP}		After Turn-on, V _{FB} = 0V	7.0	7.5	8.0	V
t _{S/S}	Internal Soft-Start Time	V _{STR} = 40V, V _{CC} Sweep		15		ms
Burst-Mode Section						
V _{BURH}	Burst-Mode Voltage	V _{CC} = 14V, V _{FB} Sweep	0.39	0.45	0.51	V
V _{BURL}			0.26	0.30	0.34	V
V _{HYS}				150		mV
Protection Section						
I _{LIM}	Peak Drain Current Limit	di/dt = 300mA/μs	3.15	3.50	3.85	A
V _{SD}	Shutdown Feedback Voltage	V _{CC} = 14V, V _{FB} Sweep	6.45	7.00	7.55	V
I _{DELAY}	Shutdown Delay Current	V _{CC} = 14V, V _{FB} = 4V	1.2	2.0	2.8	μA
t _{LEB}	Leading-Edge Blanking Time ⁽¹²⁾⁽¹⁴⁾			300		ns
V _{OVP}	Over-Voltage Protection	V _{CC} Sweep	23.0	24.5	26.0	V
t _{OSP}	Output-Short Protection ⁽¹²⁾	Threshold Time	0.7	1.0	1.3	μs
V _{OSP}		Threshold V _{FB}	1.8	2.0	2.2	V
t _{OSP_FB}		V _{FB} Blanking Time	2.0	2.5	3.0	μs
T _{SD}	Thermal Shutdown Temperature ⁽¹²⁾	Shutdown Temperature	130	140	150	°C
T _{HYS}		Hysteresis		60		°C

Continued on the following page...

Electrical Characteristics (Continued)T_J = 25°C unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Total Device Section						
I _{OP}	Operating Supply Current, (Control Part in Burst Mode)	V _{CC} = 14V, V _{FB} = 0V	0.3	0.4	0.5	mA
I _{OPS}	Operating Switching Current, (Control Part and SenseFET Part)	V _{CC} = 14V, V _{FB} = 2V	1.1	1.5	1.9	mA
I _{START}	Start Current	V _{CC} =11V (Before V _{CC} Reaches V _{START})	85	120	155	μA
I _{CH}	Startup Charging Current	V _{CC} = V _{FB} = 0V, V _{STR} = 40V	0.7	1.0	1.3	mA
V _{STR}	Minimum V _{STR} Supply Voltage	V _{CC} = V _{FB} = 0V, V _{STR} Sweep		26		V

Notes:

12. Although these parameters are guaranteed, they are not 100% tested in production.
 13. Average value.
 14. t_{LEB} includes gate turn-on time.

Comparison of FSGM0765R and FSD176MRT

Function	FSGM0765R	FSD176MRT	Advantages of FSD176MRT
Random Frequency Fluctuation		Built-in	Low EMI
Operating Current	1.6mA	0.4mA	Very low standby power

Typical Performance Characteristics

Characteristic graphs are normalized at $T_A=25^\circ\text{C}$.

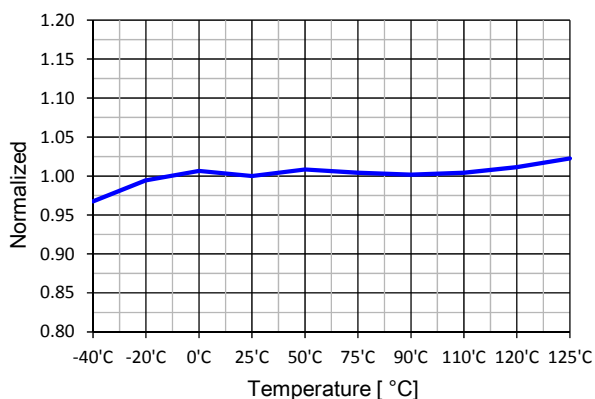


Figure 5. Operating Supply Current (I_{OP}) vs. T_A

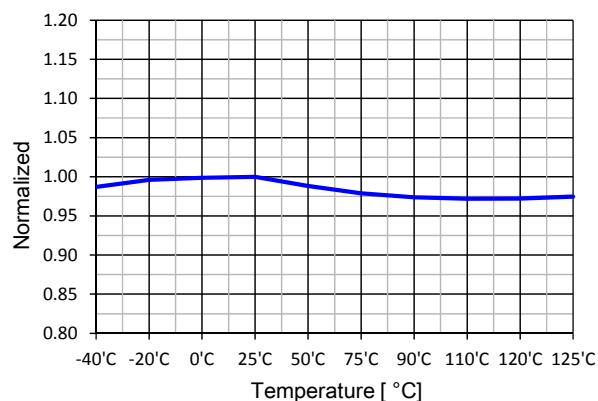


Figure 6. Operating Switching Current (I_{OPS}) vs. T_A

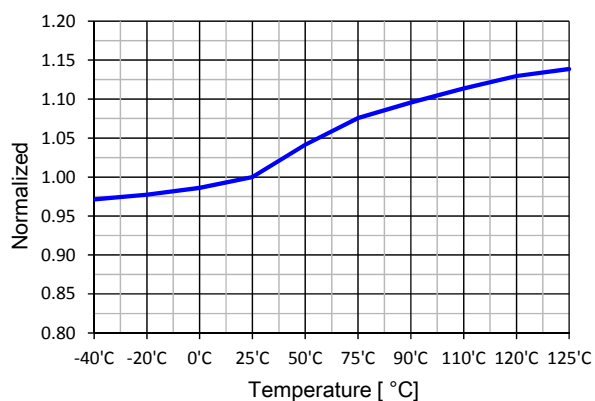


Figure 7. Startup Charging Current (I_{CH}) vs. T_A

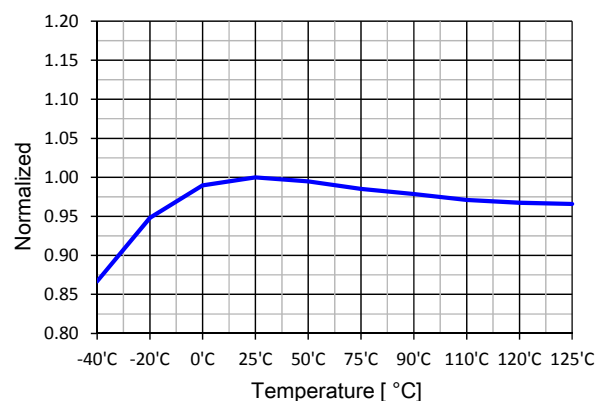


Figure 8. Peak Drain Current Limit (I_{LIM}) vs. T_A

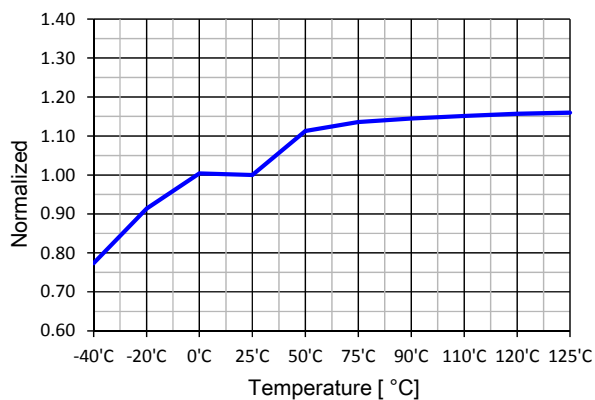


Figure 9. Feedback Source Current (I_{FB}) vs. T_A

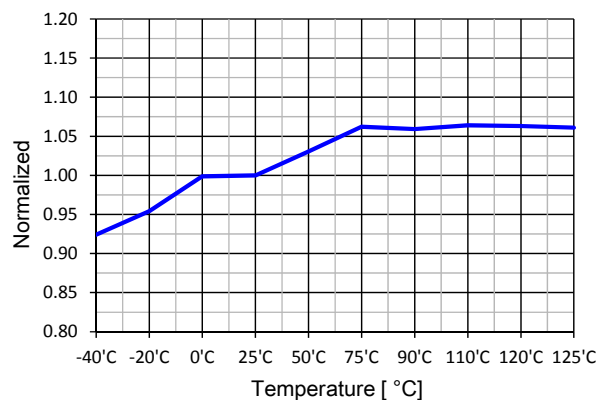


Figure 10. Shutdown Delay Current (I_{DELAY}) vs. T_A

Typical Performance Characteristics

Characteristic graphs are normalized at $T_A=25^\circ\text{C}$.

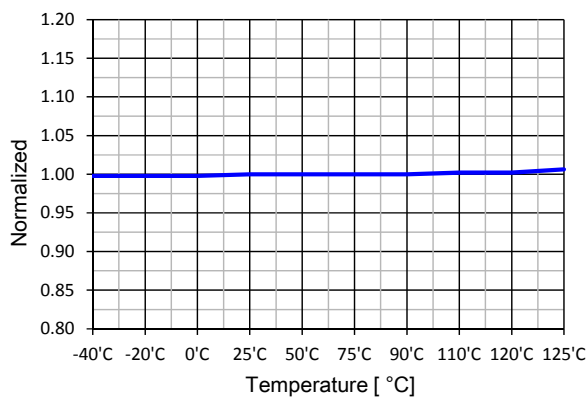


Figure 11. UVLO Threshold Voltage (V_{START}) vs. T_A

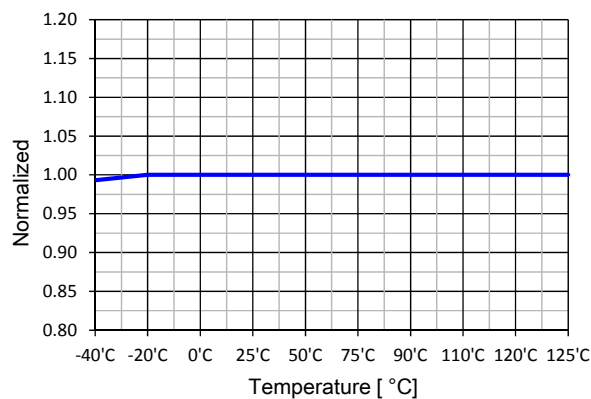


Figure 12. UVLO Threshold Voltage (V_{STOP}) vs. T_A

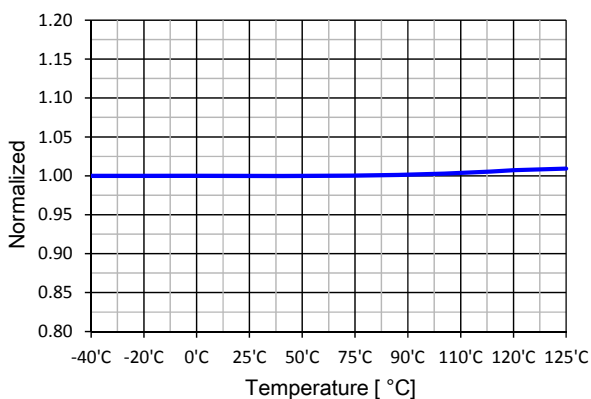


Figure 13. Shutdown Feedback Voltage (V_{SD}) vs. T_A

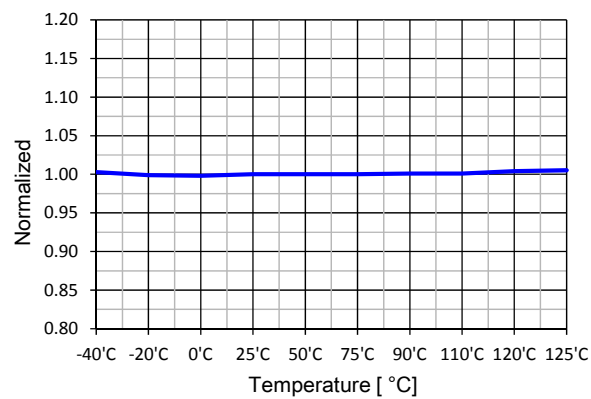


Figure 14. Over-Voltage Protection (V_{OVP}) vs. T_A

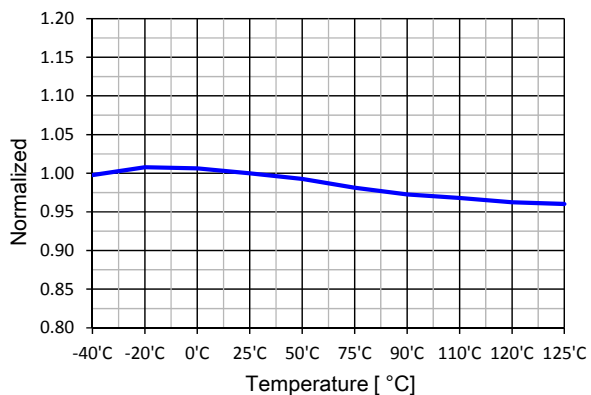


Figure 15. Switching Frequency (f_s) vs. T_A

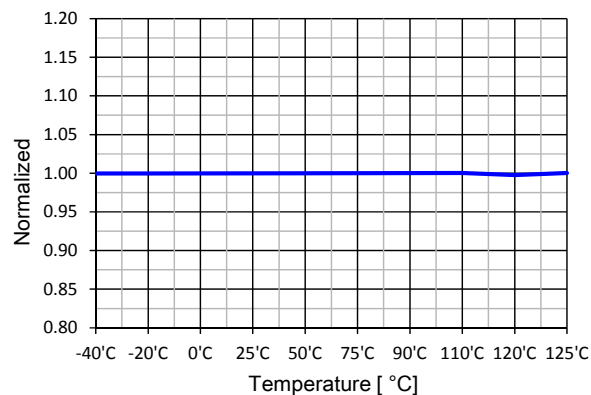


Figure 16. Maximim Duty Ratio (D_{MAX}) vs. T_A

4. Protection Circuits: The FSD176MRT has several self-protective functions, such as Overload Protection (OLP), Abnormal Over-Current Protection (AOCP), Output-Short Protection (OSP), Over-Voltage Protection (OVP), and Thermal Shutdown (TSD). All the protections are implemented as auto-restart. Once a fault condition is detected, switching is terminated and the SenseFET remains off. This causes V_{CC} to fall. When V_{CC} falls to the Under-Voltage Lockout (UVLO) stop voltage of 7.5V, the protection is reset and the startup circuit charges the V_{CC} capacitor. When V_{CC} reaches the start voltage of 12.0V, the FSD176MRT resumes normal operation. If the fault condition is not removed, the SenseFET remains off and V_{CC} drops to stop voltage again. In this manner, the auto-restart can alternately enable and disable the switching of the power SenseFET until the fault condition is eliminated. Because these protection circuits are fully integrated into the IC without external components, the reliability is improved without increasing cost.

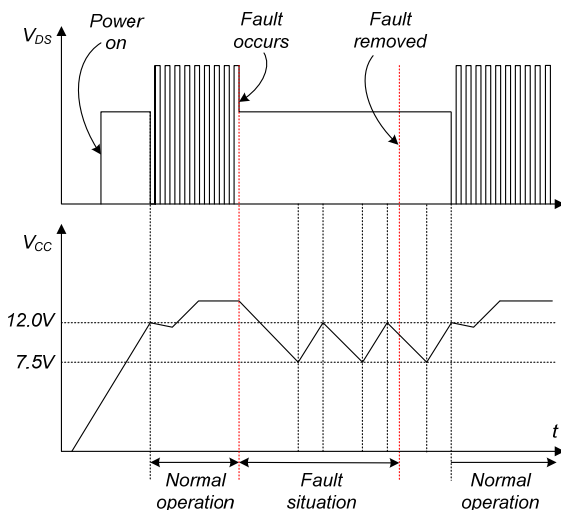


Figure 19. Auto-Restart Protection Waveforms

4.1 Overload Protection (OLP): Overload is defined as the load current exceeding its normal level due to an unexpected abnormal event. In this situation, the protection circuit should trigger to protect the SMPS. However, even when the SMPS is in normal operation, the overload protection circuit can be triggered during load transition. To avoid this undesired operation, the overload protection circuit is designed to trigger only after a specified time to determine whether it is a transient situation or a true overload situation. Because of the pulse-by-pulse current limit capability, the maximum peak current through the SenseFET is limited and, therefore, the maximum input power is restricted with a given input voltage. If the output consumes more than this maximum power, the output voltage (V_{OUT}) decreases below the set voltage. This reduces the current through the opto-coupler LED, which also reduces the opto-coupler transistor current, thus increasing the feedback voltage (V_{FB}). If V_{FB} exceeds 2.5V, D1 is blocked and the 2.0 μ A current source starts to charge C_{FB} slowly up. In this condition, V_{FB} continues

increasing until it reaches 7.0V, when the switching operation is terminated, as shown in Figure 20. The delay for shutdown is the time required to charge C_{FB} from 2.5V to 7.0V with 2.0 μ A. A 25 ~ 50ms delay is typical for most applications. This protection is implemented in auto-restart mode.

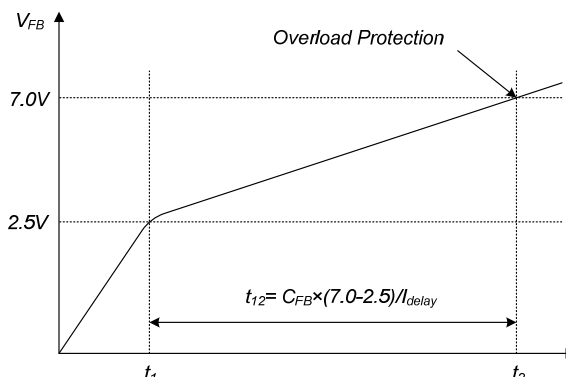


Figure 20. Overload Protection

4.2 Abnormal Over-Current Protection (AOCP): When the secondary rectifier diodes or the transformer pins are shorted, a steep current with extremely high di/dt can flow through the SenseFET during the minimum turn-on time. Overload protection is not enough to protect the FSD176MRT in that abnormal case; since severe current stress is imposed on the SenseFET until OLP is triggered. The FSD176MRT internal AOCP circuit is shown in Figure 21. When the gate turn-on signal is applied to the power SenseFET, the AOCP block is enabled and monitors the current through the sensing resistor. The voltage across the resistor is compared with a preset AOCP level. If the sensing resistor voltage is greater than the AOCP level, the set signal is applied to the S-R latch, resulting in the shutdown of the SMPS.

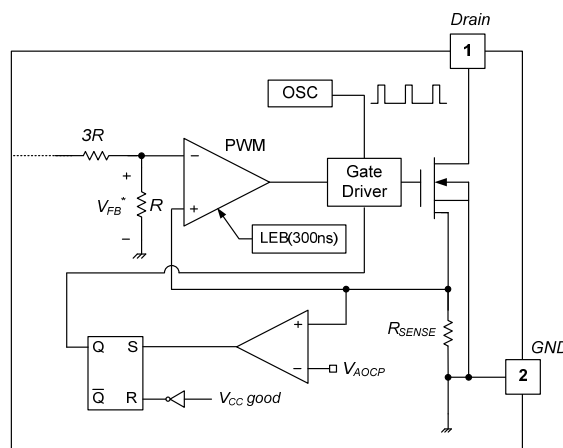


Figure 21. Abnormal Over-Current Protection

4.3. Output-Short Protection (OSP): If the output is shorted, steep current with extremely high di/dt can flow through the SenseFET during the minimum turn-on time. Such a steep current brings high-voltage stress on the drain of the SenseFET when turned off. To protect the device from this abnormal condition, OSP is included. It is comprised of detecting V_{FB} and SenseFET turn-on time. When the V_{FB} is higher than 2.0V and the SenseFET turn-on time is lower than 1.0 μ s, the FSD176MRT recognizes this condition as an abnormal error and shuts down PWM switching until V_{CC} reaches V_{START} again. An abnormal condition output short is shown in Figure 22.

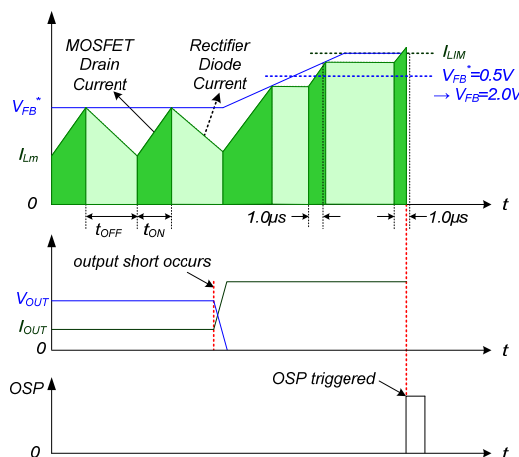


Figure 22. Output-Short Protection

4.4 Over-Voltage Protection (OVP): If the secondary-side feedback circuit malfunctions or a solder defect causes an opening in the feedback path, the current through the opto-coupler transistor becomes almost zero. Then V_{FB} climbs up in a similar manner to the overload situation, forcing the preset maximum current to be supplied to the SMPS until the overload protection is triggered. Because more energy than required is provided to the output, the output voltage may exceed the rated voltage before the overload protection is triggered, resulting in the breakdown of the devices in the secondary side. To prevent this situation, an OVP circuit is employed. In general, the V_{CC} is proportional to the output voltage and the FSD176MRT uses V_{CC} instead of directly monitoring the output voltage. If V_{CC} exceeds 24.5V, an OVP circuit is triggered, resulting in the termination of the switching operation. To avoid undesired activation of OVP during normal operation, V_{CC} should be designed to be below 24.5V.

4.5 Thermal Shutdown (TSD): The SenseFET and the control IC on a die in one package makes it easier for the control IC to detect the over temperature of the SenseFET. If the temperature exceeds ~140°C, the thermal shutdown is triggered and stops operation. The FSD176MRT operates in auto-restart mode until the temperature decreases to around 75°C, when normal operation resumes.

5. Soft Burst-Mode Operation: To minimize power dissipation in Standby Mode, the FSD176MRT enters Burst-Mode operation. As the load decreases, the feedback voltage decreases. The device automatically enters Burst Mode when the feedback voltage drops below V_{BURL} (300mV), as shown in Figure 23. At this point, switching stops and the output voltages start to drop at a rate dependent on standby current load. This causes the feedback voltage to rise. Once it passes V_{BURH} (450mV), switching resumes. The feedback voltage then falls and the process repeats. Burst Mode alternately enables and disables switching of the SenseFET, reducing switching loss in Standby Mode.

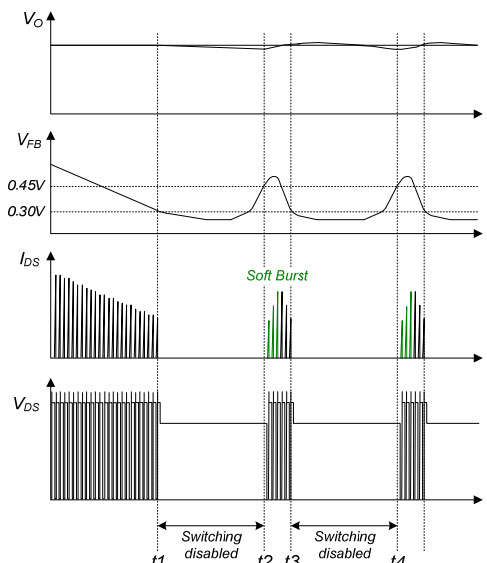


Figure 23. Burst-Mode Operation

6. Random Frequency Fluctuation (RFF): Fluctuating switching frequency of an SMPS can reduce EMI by spreading the energy over a wide frequency range. The amount of EMI reduction is directly related to the switching frequency variation, which is limited internally. The switching frequency is determined randomly by external feedback voltage and an internal free-running oscillator at every switching instant. This random frequency fluctuation scatters the EMI noise around typical switching frequency (67kHz) effectively and can reduce the cost of the input filter included to meet the EMI requirements (e.g. EN55022).

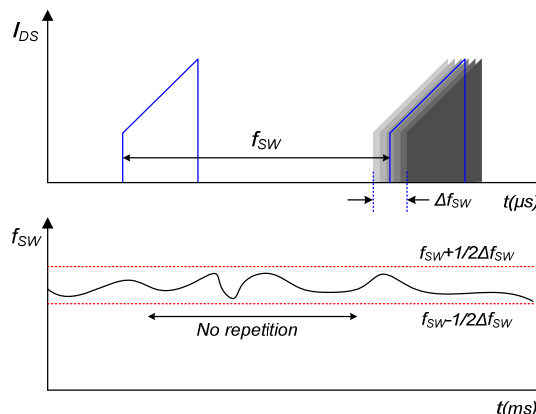


Figure 24. Random Frequency Fluctuation

Typical Application Circuit

Application	Input Voltage	Rated Output	Rated Power
LCD Monitor	85 ~ 265V _{AC}	5.0V (3A)	64W
Power Supply		14.0V (3.5A)	

Key Design Notes:

1. The delay for overload protection is designed to be about 30ms with C105 (8.2nF). OLP time between 39ms (12nF) and 46ms (15nF) is recommended.
2. The SMD-type capacitor (C106) must be placed as close as possible to the V_{CC} pin to avoid malfunction by abrupt pulsating noises and to improve ESD and surge immunity. Capacitance between 100nF and 220nF is recommended.

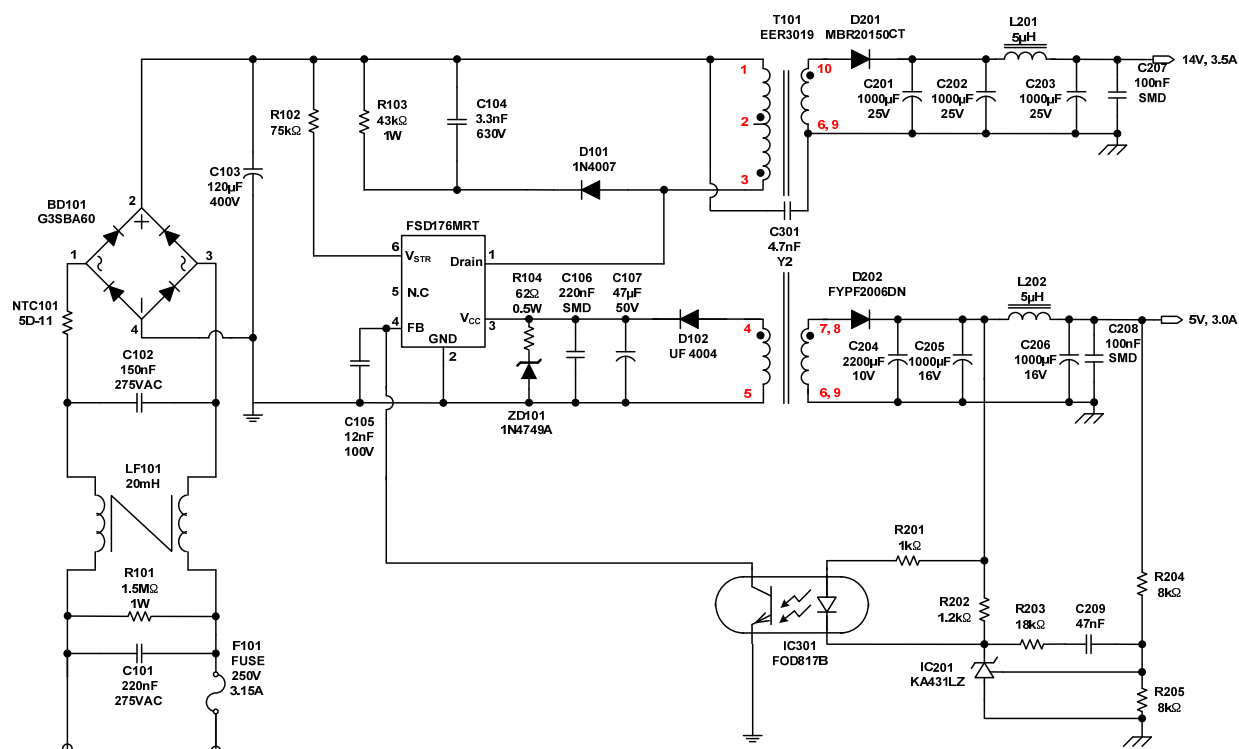


Figure 25. Schematic

Transformer Specification

- Core: EER3019 ($A_e = 134 \text{ mm}^2$)
- Bobbin: EER3019

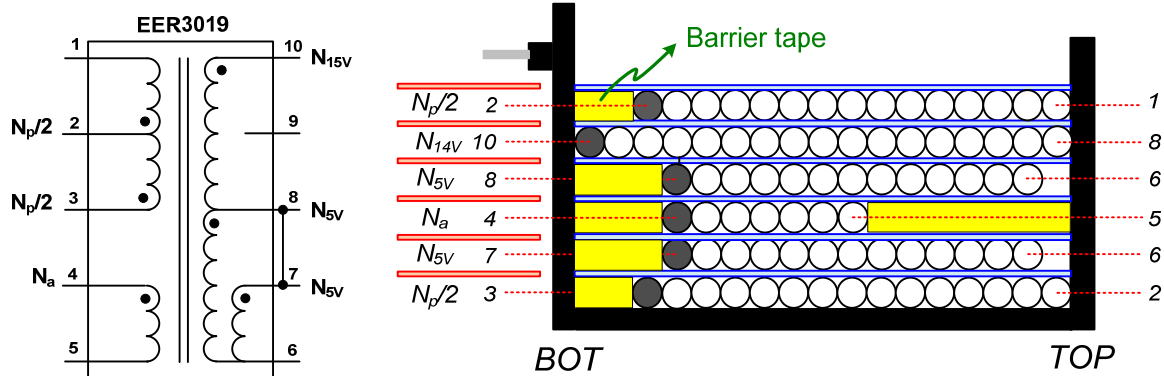


Figure 26. Transformer Specification

Table 1. Winding specification

	Pin(S → F)	Wire	Turns	Winding Method	Barrier Tape		
					TOP	BOT	Ts
$N_p/2(\text{BOT})$	3 → 2	0.4φ×1	18	Solenoid Winding		2.0mm	1
Insulation: Polyester Tape t = 0.025mm, 2 Layers							
N_{5V}	7 → 6	0.4φ×3 (TIW)	3	Solenoid Winding		3.0mm	1
Insulation: Polyester Tape t = 0.025mm, 2 Layers							
N_a	4 → 5	0.20φ×1	8	Solenoid Winding	4.0mm	3.0mm	1
Insulation: Polyester Tape t = 0.025mm, 2 Layers							
N_{5V}	8 → 6	0.4φ×3 (TIW)	3	Solenoid Winding		3.0mm	1
Insulation: Polyester Tape t = 0.025mm, 2 Layers							
N_{14V}	10 → 8	0.4φ×3 (TIW)	5	Solenoid Winding			1
Insulation: Polyester Tape t = 0.025mm, 2 Layers							
$N_p/2(\text{TOP})$	2 → 1	0.4φ×1	18	Solenoid Winding		2.0mm	1
Insulation: Polyester Tape t = 0.025mm, 2 Layers							

Table 2. Electrical Characteristics

	Pin	Specification	Remark
Inductance	1 – 3	465μH ±6%	67kHz, 1V
Leakage	1 – 3	10μH Maximum	Short all other pins

Table 3. Bill of Materials

Part #	Value	Note	Part #	Value	Note
Fuse			Capacitor		
F101	250V 3.15A		C101	220nF/275V	Box (Pilkor)
NTC			C102	150nF/275V	Box (Pilkor)
NTC101	5D-11	DSC	C103	120μF/400V	Electrolytic (SamYoung)
Resistor			C104	3.3nF/630V	Film (Sehwa)
R101	1.5MΩ, J	1W	C105	12nF/100V	Film (Sehwa)
R103	43kΩ, J	1W	C106	220nF	SMD (2012)
R201	1kΩ, F	1/4W, 1%	C107	47μF/50V	Electrolytic (SamYoung)
R202	1.2kΩ, F	1/4W, 1%	C201	1000μF/25V	Electrolytic (SamYoung)
R203	18kΩ, F	1/4W, 1%	C202	1000μF/25V	Electrolytic (SamYoung)
R204	8kΩ, F	1/4W, 1%	C203	1000μF/25V	Electrolytic (SamYoung)
R205	8kΩ, F	1/4W, 1%	C204	2200μF/10V	Electrolytic (SamYoung)
			C205	1000μF/16V	Electrolytic (SamYoung)
			C206	1000μF/16V	Electrolytic (SamYoung)
IC			C207	100nF	SMD (2012)
			C208	100nF	SMD (2012)
SMPS	FSD176MRT	Fairchild Semiconductor	C301	4.7nF/Y2	Y-cap (Samhwa)
IC201	KA431LZ	Fairchild Semiconductor	Inductor		
IC301	FOD817B	Fairchild Semiconductor	LF101	20mH	Line Filter 0.5Ø
Diode			L201	5μH	5A Rating
D101	1N4007	Vishay	L202	5μH	5A Rating
D102	UF4004	Vishay	Transformer		
ZD101	1N4750	Vishay	T101	465μH	
D201	MBR20150CT	Fairchild Semiconductor			
D202	FYPF2006DN	Fairchild Semiconductor			
BD101	G3SBA60	Vishay			

Physical Dimensions

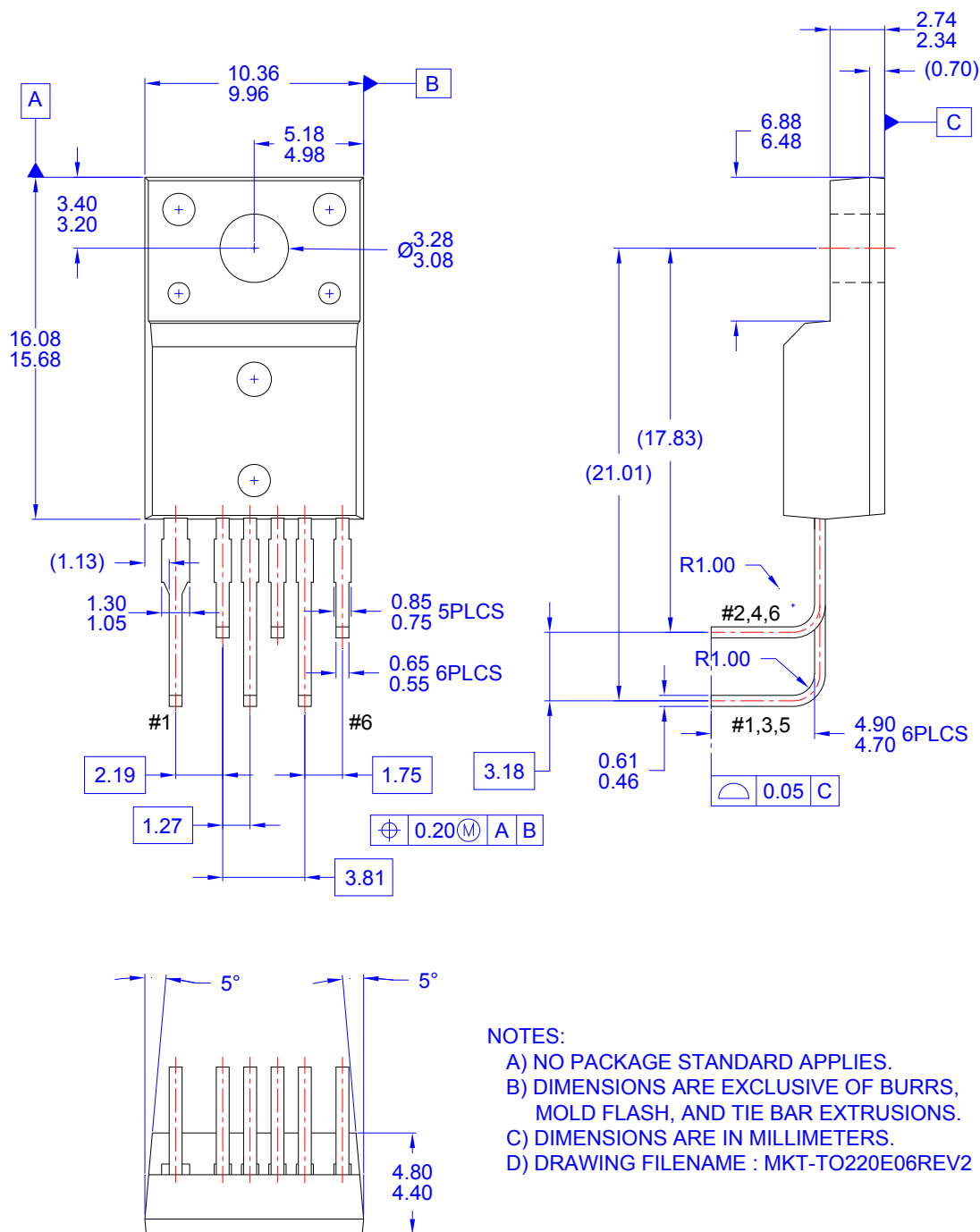


Figure 27. 6-Lead, TO220, Fullpack, Formed

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Physical Dimensions

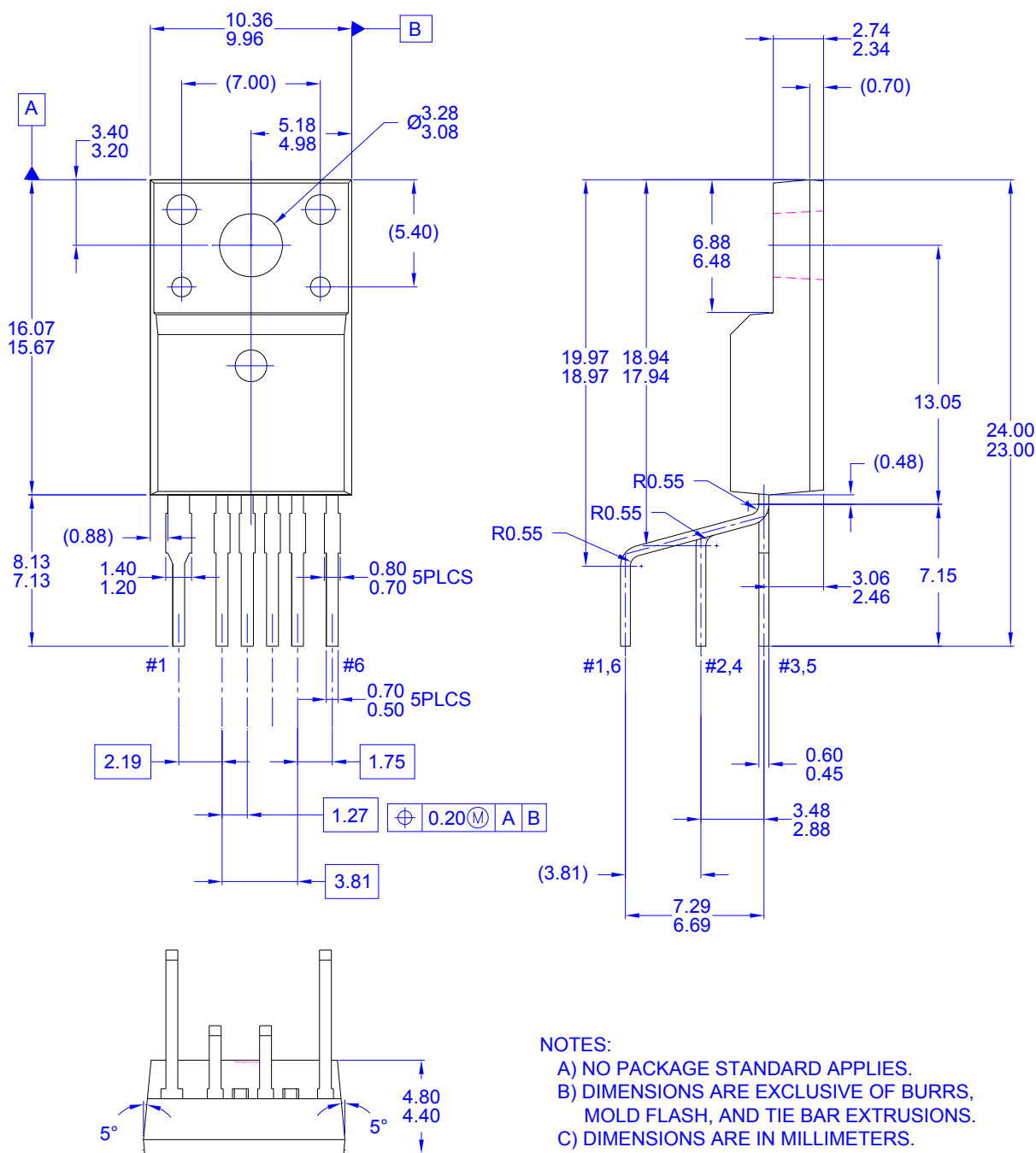


Figure 28. 6-Lead, TO220, Fullpack, U-Forming, 2 DAP

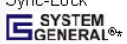
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BitSiC®	Green FPS™	Programmable Active Droop™	TinyCalc™
Build it Now™	Green FPS™ e-Series™	QFET®	TinyLogic®
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CTL™	ISOPLANAR™	 ™	TinyWire™
Current Transfer Logic™	Making Small Speakers Sound Louder and Better™	Saving our world, 1mW/WkW at a time™	TransiC®
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Fairchild Semiconductor®	MotionMax™	SuperSOT™-3	UniFET™
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FACT®	mWSaver™	SuperSOT™-8	VisualMax™
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